

High Efficiency Recovery rectifiers

Major Ratings and Characteristics

I _{F(AV)}	3.0A
V _{RRM}	50 V to 1000 V
I _{FSM}	100 A
t _{rr}	50nS,75ns
V _F	1.0V,1.3V,1.7V
T _j max.	150 °C

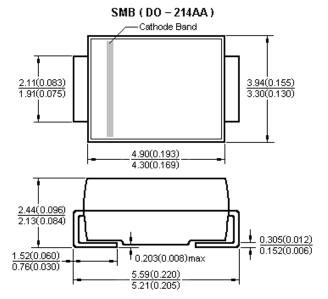
Pb SMB (DO - 214AA)

Features

- Low profile package
- Ideal for automated placement
- Glass passivated chip junction
- Ultrafast reverse recovery time
- Low switching losses, high efficiency
- High forward surge capability
- High temperatrue soldering:
 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/1 and WEEE 2002/96/EC

Mechanical Date

- Case: JEDEC DO-214ABolded plastic body over passivated chip
- Terminals: Solder plated, solderable per J-STD-002B and JESD22-B102D
- Polarity: Laser band denotes cathode end



Dimentsions in millimeters and (inchs)

Maximum Ratings & Thermal Characteristics & Electrical Characteristics

(T_Δ = 25 °C unless otherwise noted)

(1 _A = 25 °C unless otherwise noted)										
	Symbol	US3A	US3B	US3D	US3G	US3J	US3K	US3M	UNIT	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V	
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V	
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V	
Maximum average forward rectified current	I _{F(AV)}	3							Α	
Peak forward surge current 8.3 ms single half sinewave superimposed on rated load	I _{FSM}	100							Α	
Maximum instantaneous forward voltage at 3.0A	V_{F}		1.0		1.3		1.7		V	
Maximum DC reverse current $T_A = 25 ^{\circ}\mathbb{C}$ at Rated DC blocking voltage $T_A = 100 ^{\circ}\mathbb{C}$	I _R	10.0 50						μA		
Maximum reverse recovery time at $I_F = 0.5 \text{ A}$, $I_R = 1.0 \text{ A}$, $I_{rr} = 0.25 \text{ A}$	t _{rr}	50 75						nS		
Typical junction capacitance at 4.0 V ,1MHz	CJ	15					pF			
Thermal resistance from junction to lead	$R_{\theta JL}$	85							°C/ W	
Operating junction and storage temperature range	T_J , T_{STG}	–55 to +150							$^{\circ}$	



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Characteristic Curves (T_A=25 ℃ unless otherwise noted)

